STB75NF75
STP75NF75 - STP75NF75FP

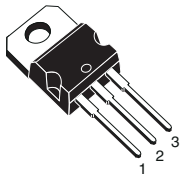
N-channel 75V - 0.0095Ω - 80A - TO-220 - TO-220FP - D²PAK
STripFET™ II Power MOSFET

General features

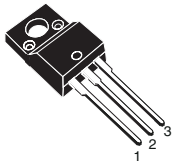
Type	V_{DSS}	$R_{DS(on)}$	I_D
STB75NF75	75V	<0.011Ω	80A(1)
STP75NF75	75V	<0.011Ω	80A(1)
STP75NF75FP	75V	<0.011Ω	80A(1)

1. Current limited by package

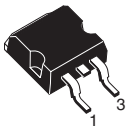
- Exceptional dv/dt capability
- 100% avalanche tested



TO-220



TO-220FP

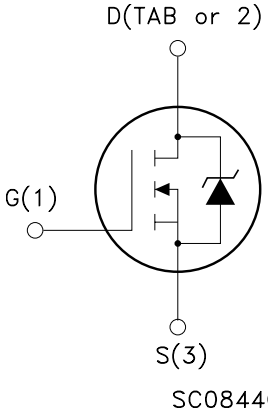


D²PAK

Description

This Power MOSFET series realized with STMicroelectronics unique STripFET™ process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency, high-frequency isolated DC-DC converters for Telecom and Computer applications. It is also intended for any applications with low gate drive requirements.

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STB75NF75T4	B75NF75	D²PAK	Tape & reel
STP75NF75	P75NF75	TO-220	Tube
STP75NF75FP	P75NF75	TO-220FP	Tube

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2 Electrical characteristics 4

2.1 Electrical characteristics (curves) 6

3 Test circuit 9

4 Package mechanical data 10

5 Packaging mechanical data 14

6 Revision history 15

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D^2PAK /TO-220	TO-220FP	
V_{DS}	Drain-source voltage (V_{GS} = 0)	75		V
V_{DGR}	Drain-gate voltage (R_{GS} = 20KΩ)	75		V
V_{GS}	Gate-source voltage	± 20		V
I_D (1)	Drain current (continuous) at T_C = 25°C	80	80	A
I_D(1)	Drain current (continuous) at T_C=100°C	70	70	A
I_{DM}(2)	Drain current (pulsed)	320	320	A
P_{TOT}	Total dissipation at T_C = 25°C	300	45	W
	Derating factor	2.0	0.3	W/°C
dv/dt (3)	Peak diode recovery voltage slope	12		V/ns
E_{AS} (4)	Single pulse avalanche energy	700		mJ
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T_C=25°C)	--	2000	V
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 175		°C

1. Current limited by package
2. Pulse width limited by safe operating area
3. I_{SD} ≤80A, di/dt ≤300A/µs, V_{DD} ≤$V_{(BR)DSS}$, T_j ≤T_{JMAX}
4. Starting T_J = 25 °C, I_D = 40A, V_{DD} = 37.5V

Table 2. Thermal data

Symbol	Parameter	Value		Unit
		D^2PAK /TO-220	TO-220FP	
R_{thJC}	Thermal resistance junction-case max	0.5	3.33	°C/W
R_{thJA}	Thermal resistance junction-ambient max	62.5		°C/W
T_l	Maximum lead temperature for soldering purpose(1)	300		°C

1. 1.6mm from case for 10sec)

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS}= 0	75			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±20V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 40A		0.0095	0.011	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} = 15V, I_D = 40A		20		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25V, f = 1 MHz, V_{GS} = 0		3700 730 240		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 60V, I_D = 80A V_{GS} =10V		117 27 47	160	nC nC nC

1. Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD}= 37.5V, I_D= 45A, R_G=4.7Ω, V_{GS}=10V *Figure 15 on page 9*		25 100 66 30		ns ns ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				80	A
I_{SDM} (1)	Source-drain current (pulsed)				320	A
V_{SD} (2)	Forward on voltage	I_{SD} = 80A, V_{GS} = 0			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 80A, di/dt = 100A/µs, V_{DD} = 25V, T_J = 150°C *Figure 17 on page 9*		132 660 10		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220 - D²PAK

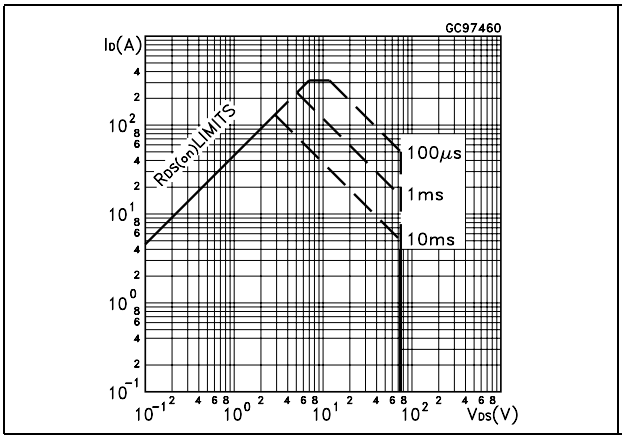


Figure 2. Thermal impedancefor TO-220 - D²PAK

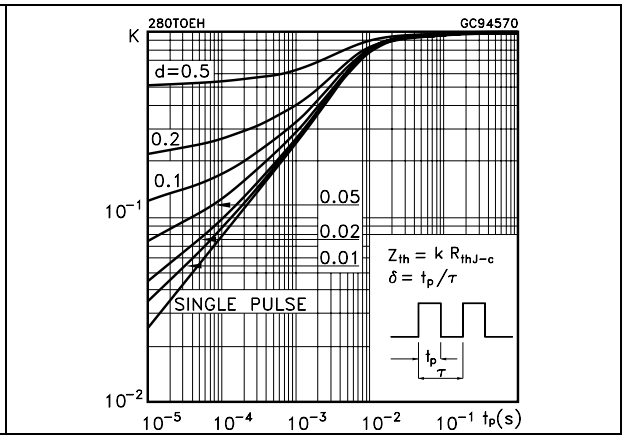


Figure 3. Safe operating area for TO-220FP

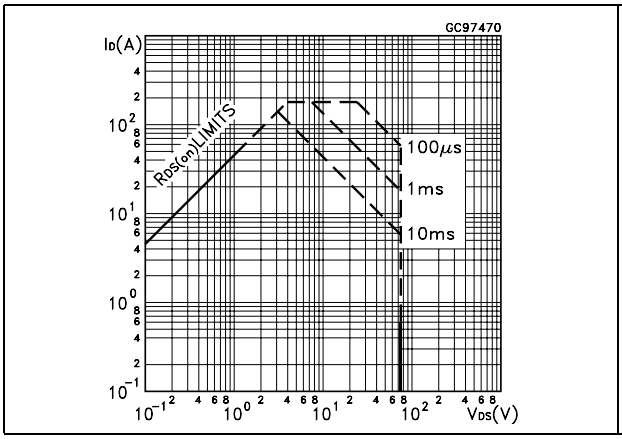


Figure 4. Thermal impedance for TO-220FP

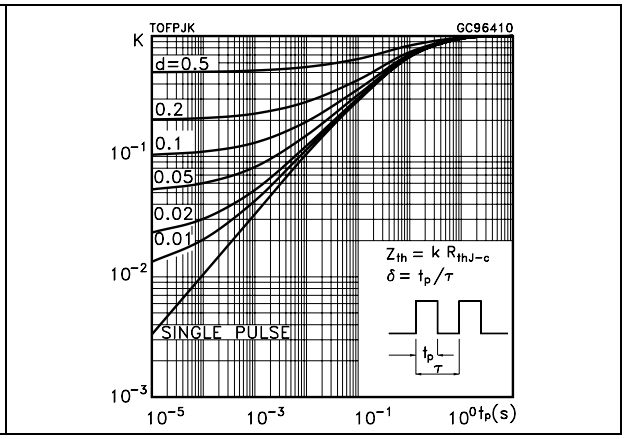


Figure 5. Output characterisics

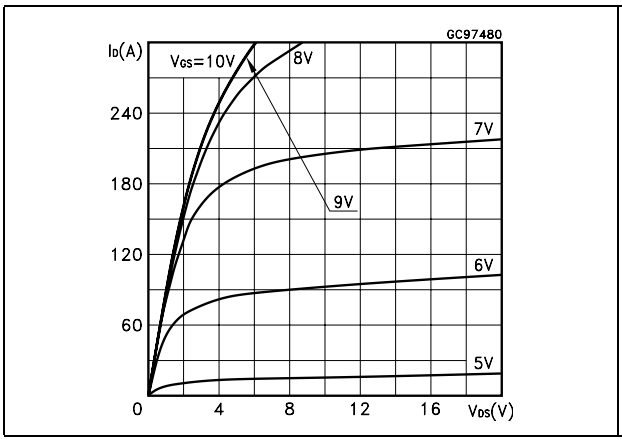


Figure 6. Transfer characteristics

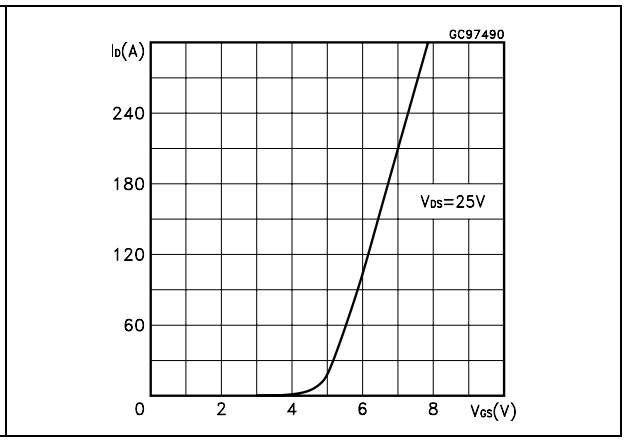


Figure 7. Transconductance

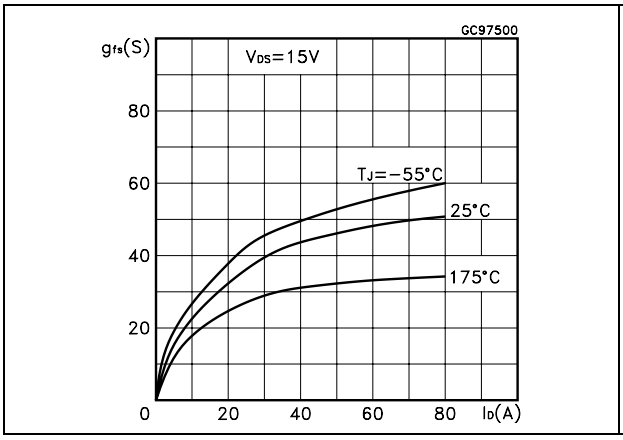


Figure 8. Static drain-source on resistance

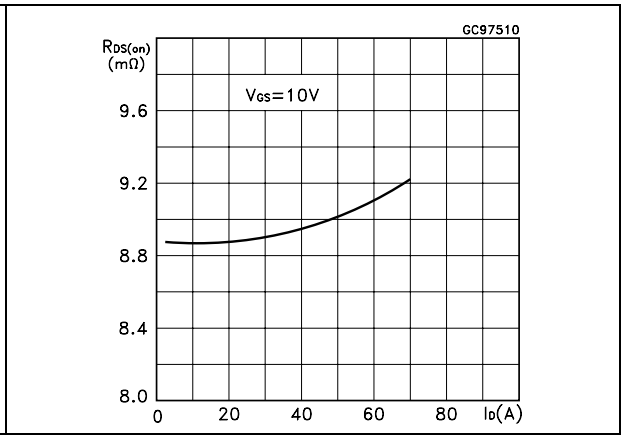


Figure 9. Gate charge vs gate-source voltage

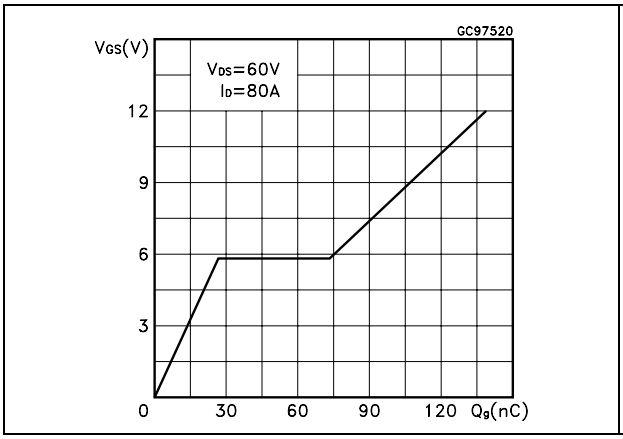


Figure 10. Capacitance variations

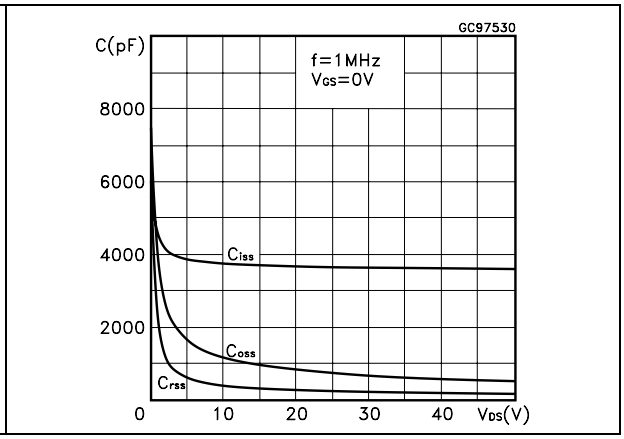


Figure 11. Normalized gate threshold voltage vs temperature

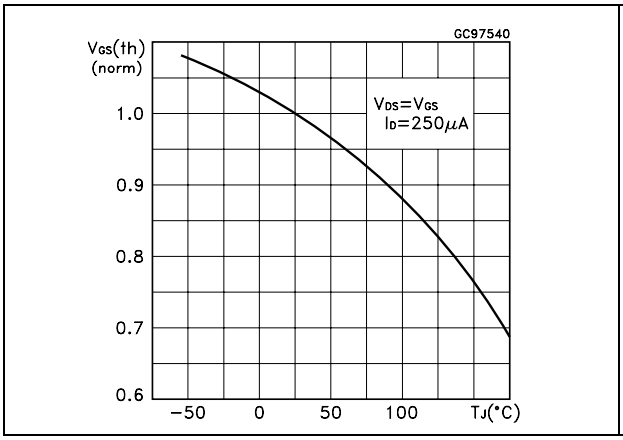


Figure 12. Normalized on resistance vs temperature

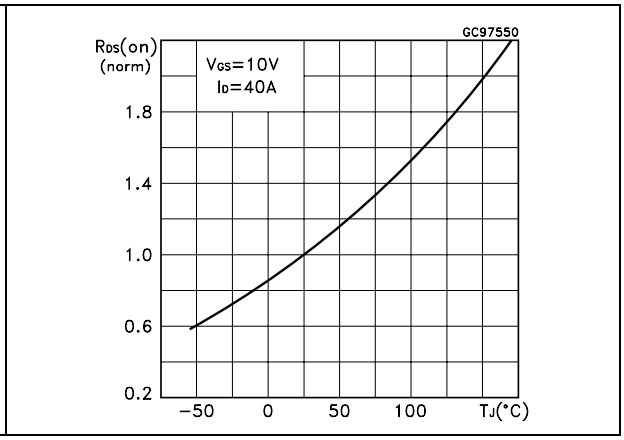


Figure 13. Source-drain diode forward characteristics

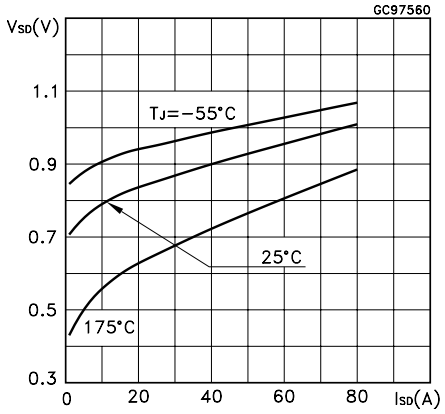
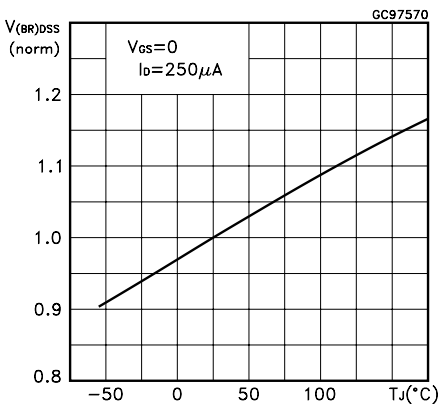


Figure 14. Normalized B_{VDSS} vs temperature



3 Test circuit

Figure 15. Switching times test circuit for resistive load

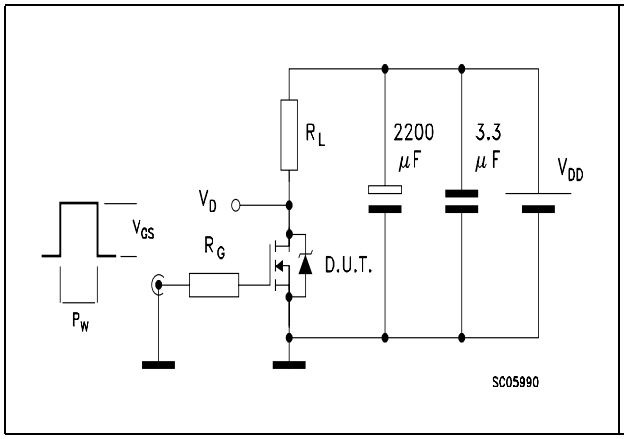


Figure 16. Gate charge test circuit

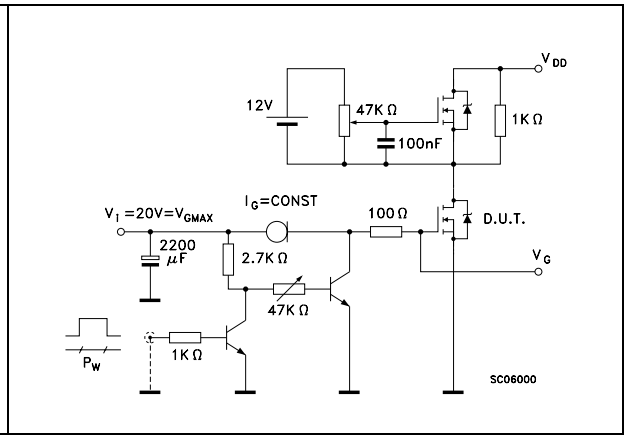


Figure 17. Test circuit for inductive load switching and diode recovery times

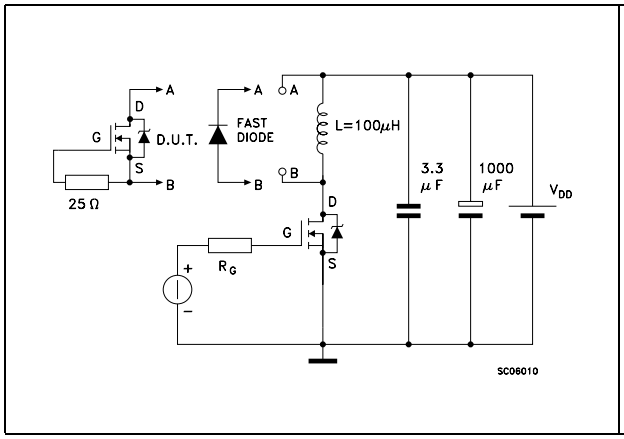


Figure 18. Unclamped inductive load test circuit

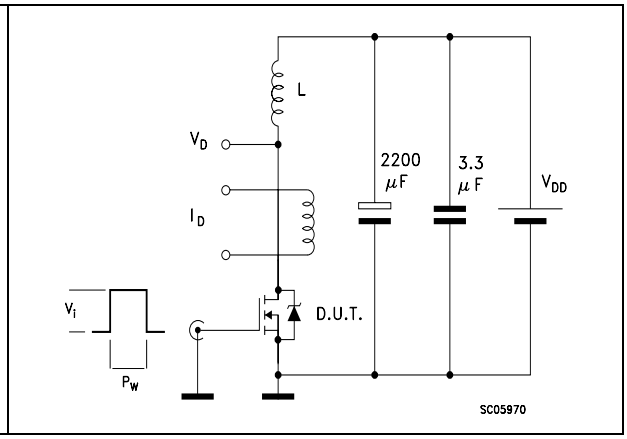
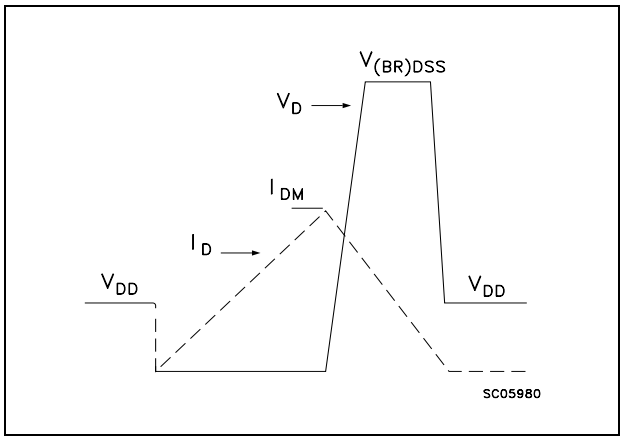


Figure 19. Unclamped inductive waveform

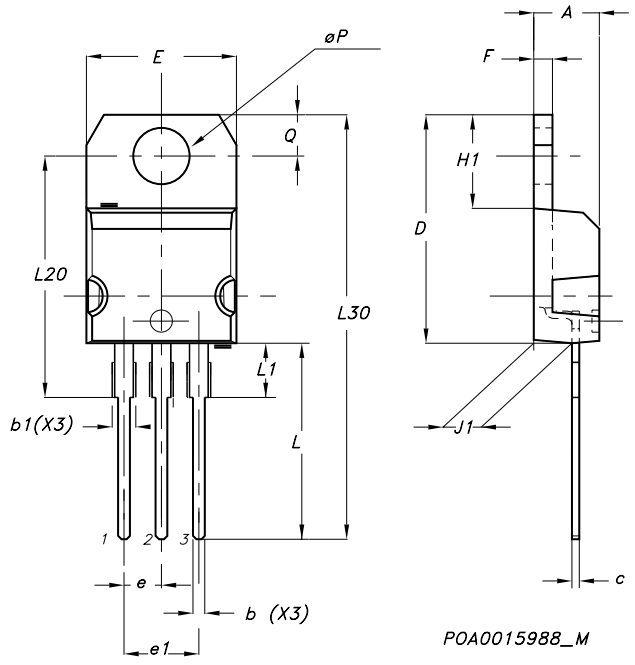


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

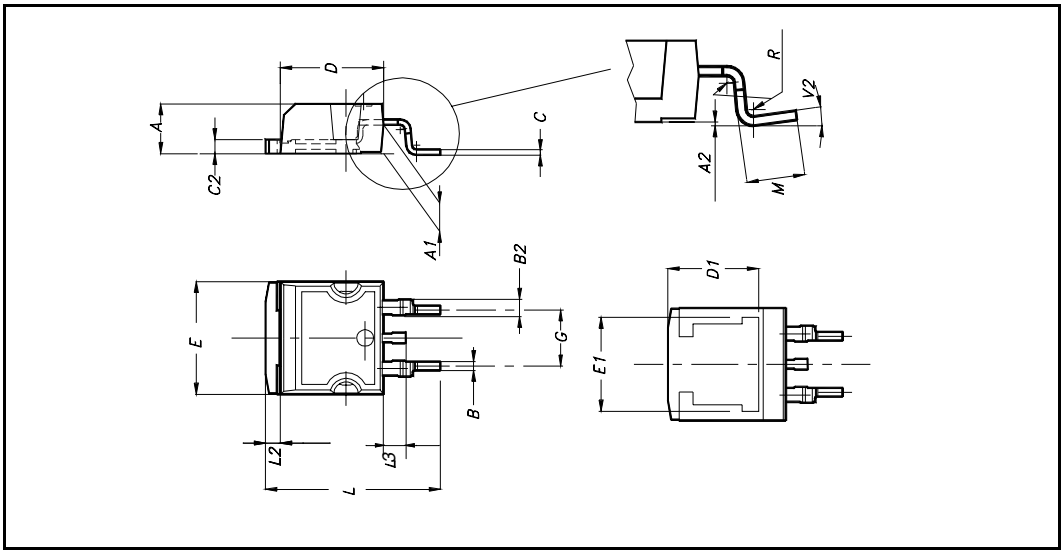
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



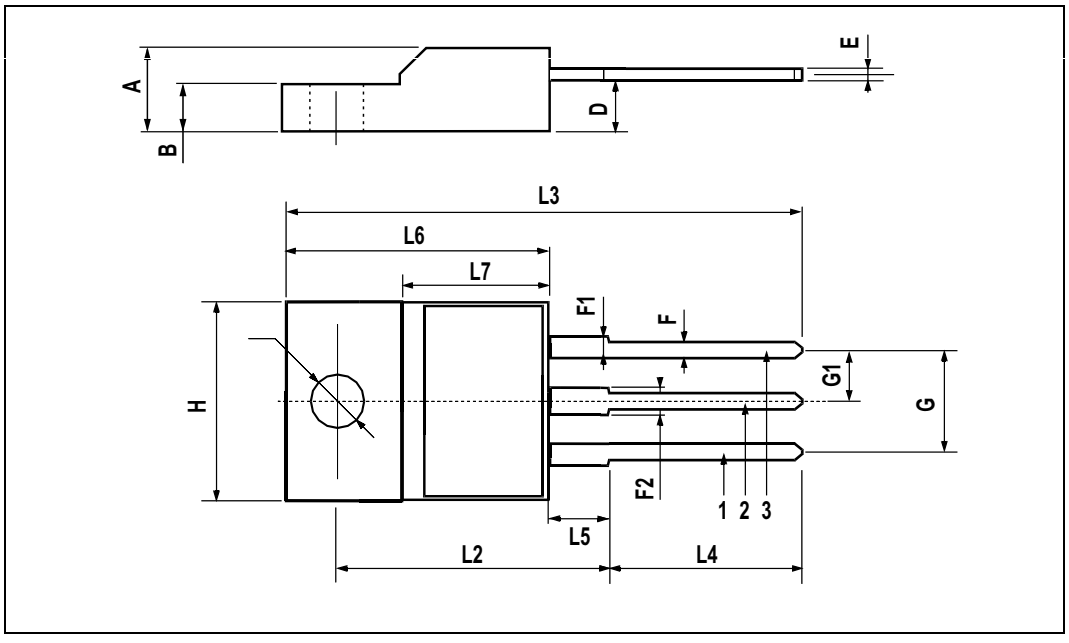
D^2PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0º		4º			



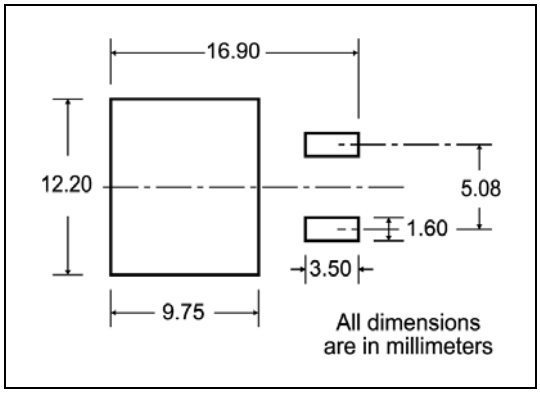
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126

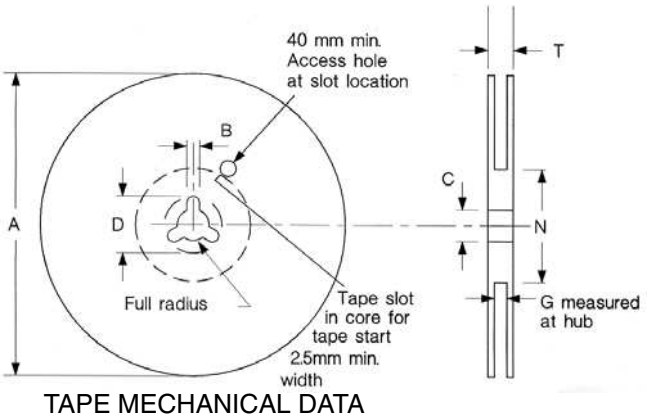


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



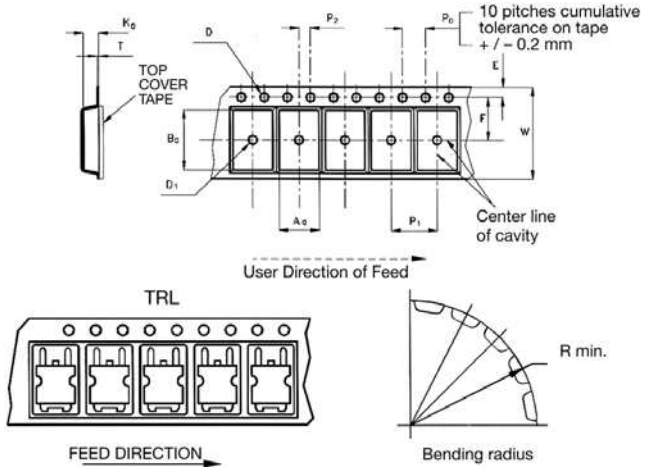
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956



* on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
03-Aug-2006	6	Complete version
15-Sep-2006	7	$R_{DS(on)}$ value update
27-Feb-2007	8	The document has been reformatted

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